


MITSUBISHI IGBT
CY20AAJ-8F

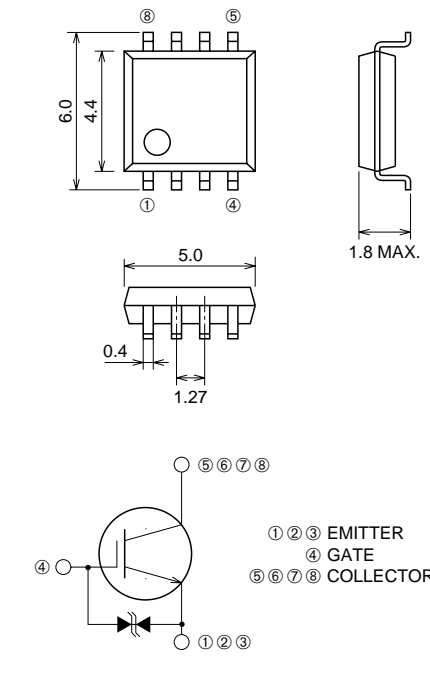
Nch IGBT for STROBE FLASHER

CY20AAJ-8F



- VCES 400V
- ICM 130A
- Drive voltage 4V

OUTLINE DRAWING Dimensions in mm



① ② ③ EMITTER
 ④ GATE
 ⑤ ⑥ ⑦ ⑧ COLLECTOR

SOP-8

APPLICATION

Strobe Flasher for camera

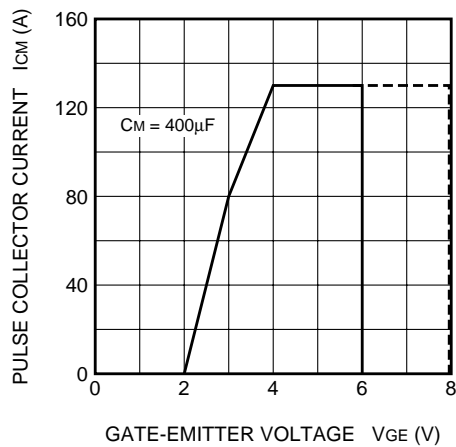
MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	V _{GE} = 0V	400	V
V _{GES}	Gate-emitter voltage	V _{CE} = 0V	±6	V
V _{GEM}	Peak gate-emitter voltage	V _{CE} = 0V, t _w = 10s	±8	V
I _{CM}	Collector current (Pulsed)	C _M = 400μF see figure1	130	A
T _j	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_j = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) CES	Collector-emitter breakdown voltage	I _C = 1mA, V _{GE} = 0V	450	—	—	V
V (BR) GES	Gate-emitter breakdown voltage	I _G = ±100μA, V _{CE} = 0V	±8	—	—	V
I _{CES}	Collector-emitter leakage current	V _{CE} = 400V, V _{GE} = 0V	—	—	10	μA
I _{GES}	Gate-emitter leakage current	V _{GE} = ±6V, V _{CE} = 0V	—	—	±10	μA
V _{GE} (th)	Gate-emitter threshold voltage	V _{CE} = 10V, I _C = 1mA	—	—	1.5	V

Figure1. MAXIMUM PULSE COLLECTOR CURRENT



APPLICATION EXAMPLE

